



Improvement of timing resolution and radiation tolerance for finely segmented AC-LGAD sensors

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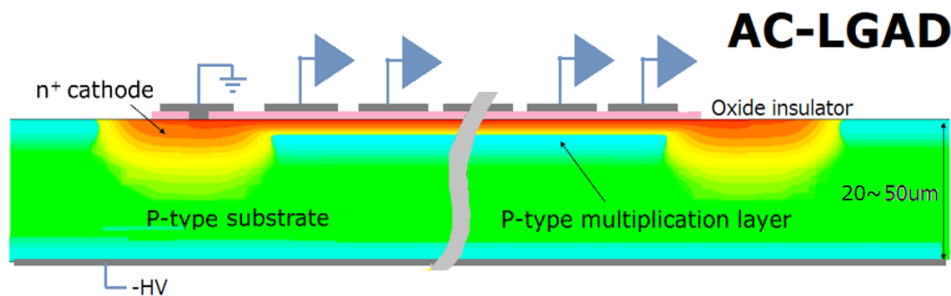


Acknowledgement:

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JSPS Kakenhi No.19H05193, 19H04393, 21H0073 and 21H01099
FJPPL (France Japan Particle Physics Laboratory)

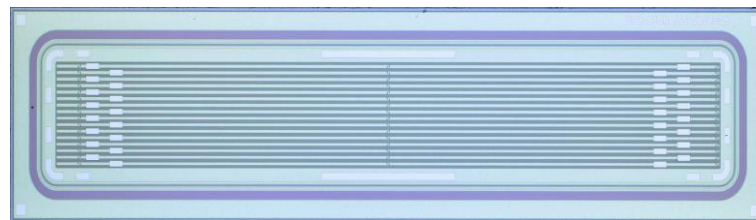
AC-LGAD : parameters to optimize

High granularity achieved by AC electrodes achieving uniform LGAD gain



- Performance evaluated of three sensor types

Strip (80um pitch x 1cm)

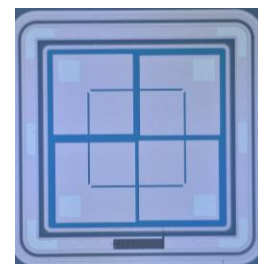
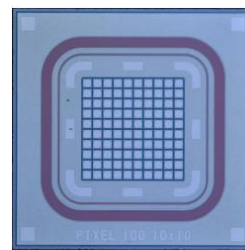


Hamamatsu Photonics:

n+ implant resistivity (Ω/sq)

C_{cp} (pF/mm^2)	40	130	400	800	1600
80	✓	✓	✓	✓	
120			✓	✓	✓
240			✓		✓
600			✓		✓

Pixel (1x1mm active:
50,100,150,200um \square)



4ch Pad

(2x2 500um \square)
- w/ slits for laser

- p+ implantation adjusted to $V_{\text{gain}} < 160 \sim 190\text{V}$ (50um †)
- active thickness : 50um, 20um

- electrode gap varied slightly

$$Q = \frac{R_{\text{imp}}}{\sqrt{1/(2\pi f C_{cp})^2 + R_{\text{imp}}^2}} \times Q_0$$



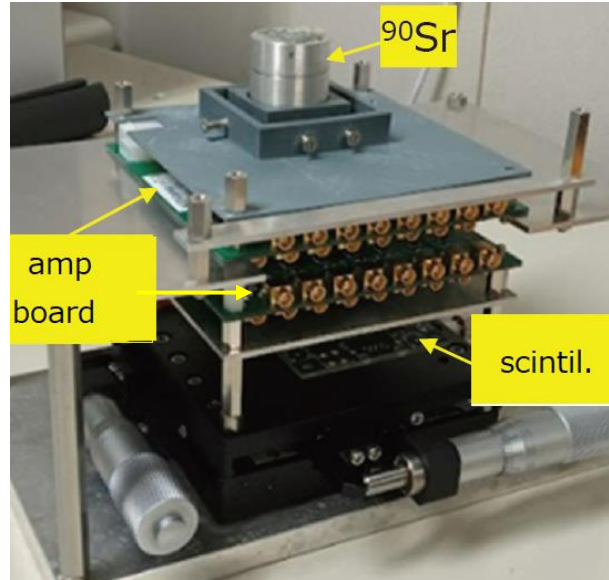
- Q larger for larger C_{cp} , R_{imp}
- large R_{imp} to suppress X-talk

Measurement system @ bench (20°C)

- Beta-ray



16-ch amp
(2-stage GALI-S66+, BW~3GHz)

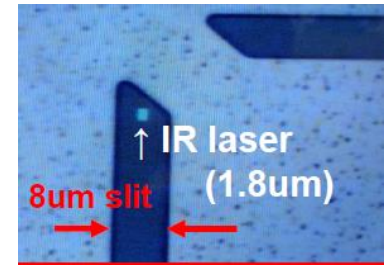


2 sensors aligned for
timing resolution study

- IR laser



KATANA10
(1064nm, 35ps PW, Jitter ~ 5 ps)



collimated

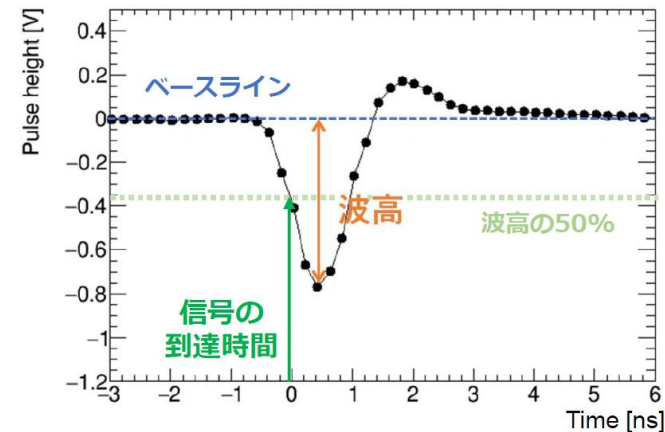
- Time reference ← or



Photek PMT240
(40mmφ, Jitter<10ps)

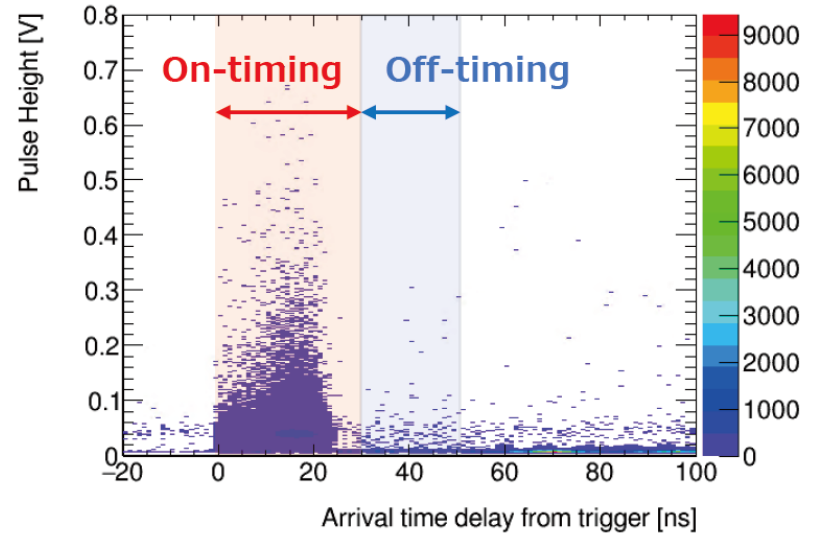
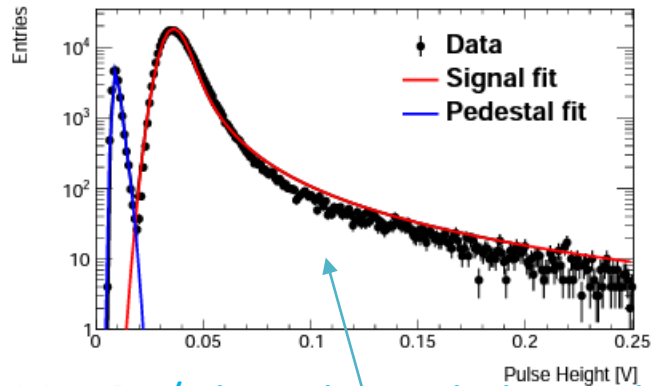
- DAQ

DT5742(16ch,5GS/s)
or
Waverunner8208HD
(2GHz, 8ch,10GS/s)

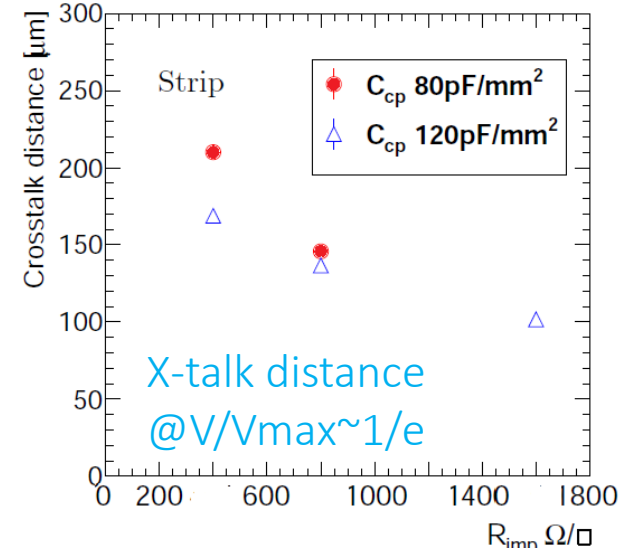
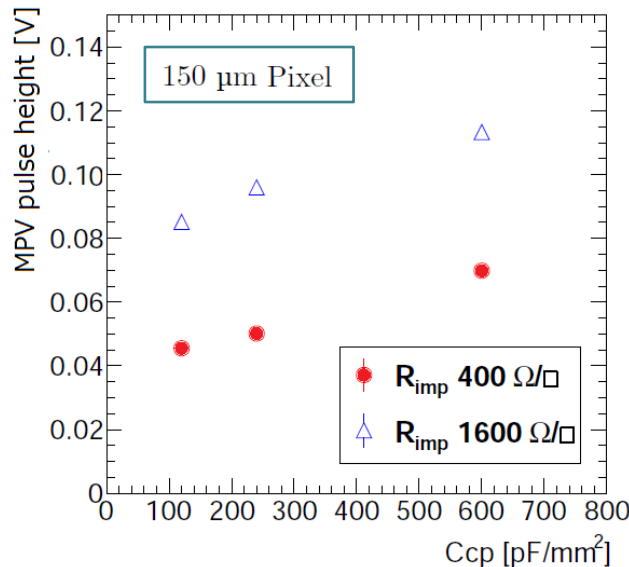
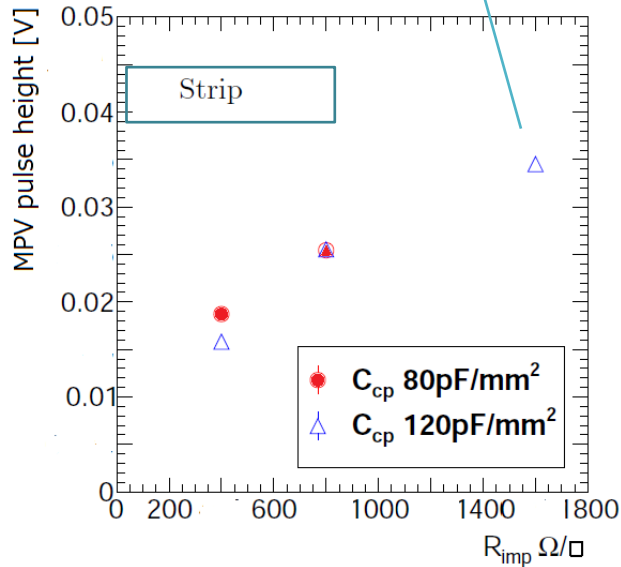


Pulse height

HV@ max V below noise increases



Max PH/trigger in on-timing region



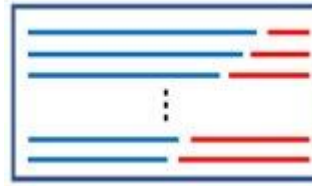
Nice signal, rms noise~1.5-2.0 mV
 Q larger for larger C_{cp} , R_{imp} , as expected
 X-talk smaller for larger R_{imp}

but

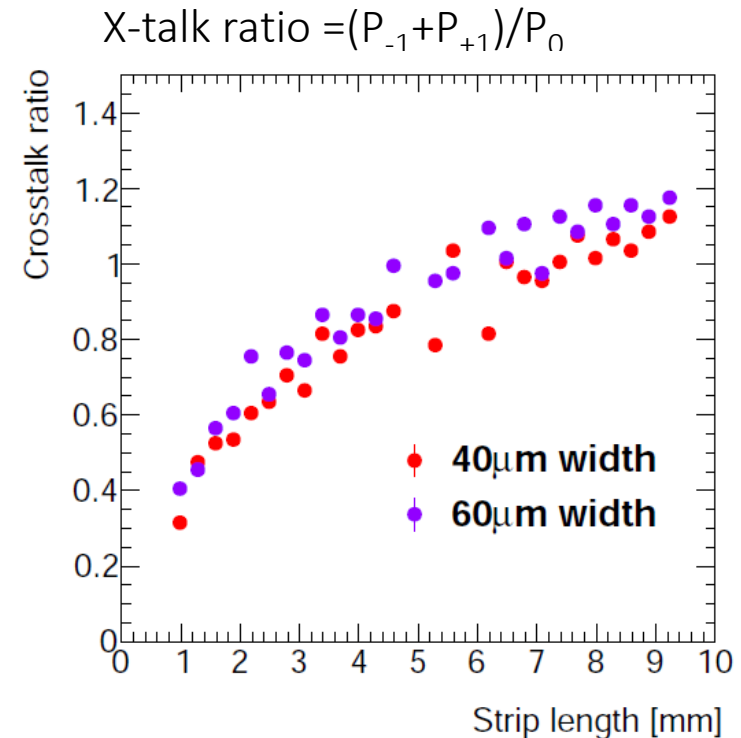
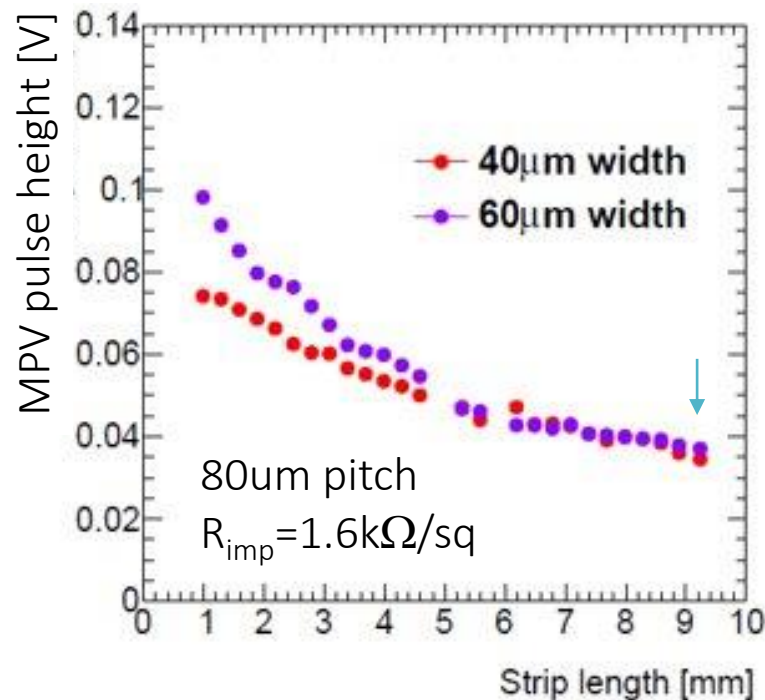
- $PH(strip) < PH(pixel)$
- weak $C_{cp}(strip)$ dependence.

Strip Pulse Height

- $PH(strip) < PH(pixel)$
- weak $C_{cp}(strip)$ dependence

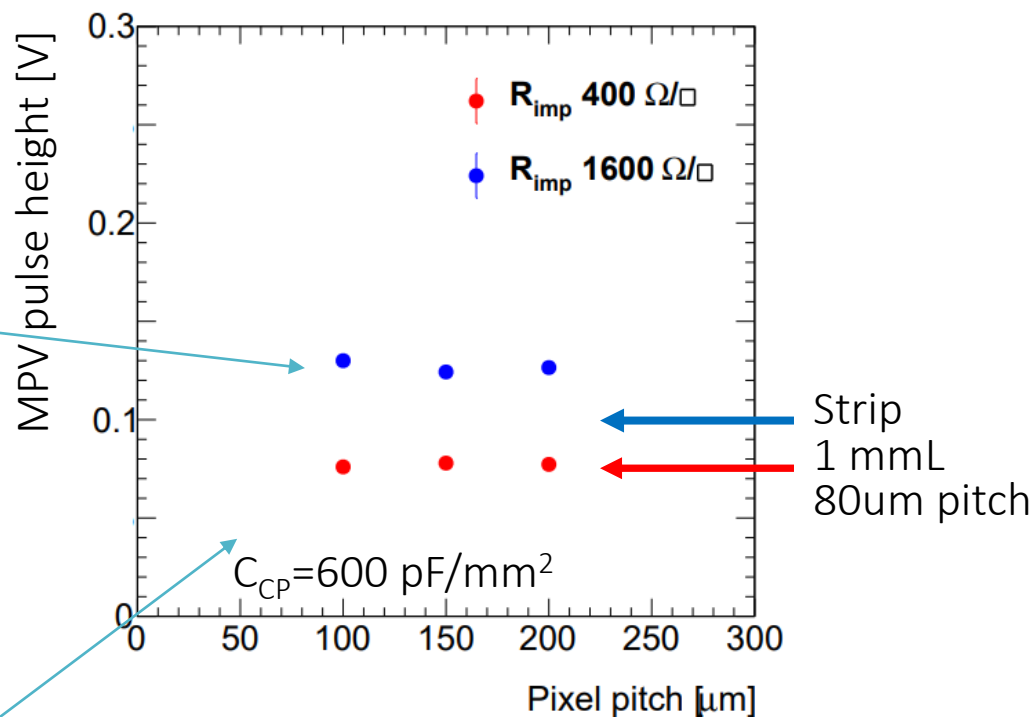
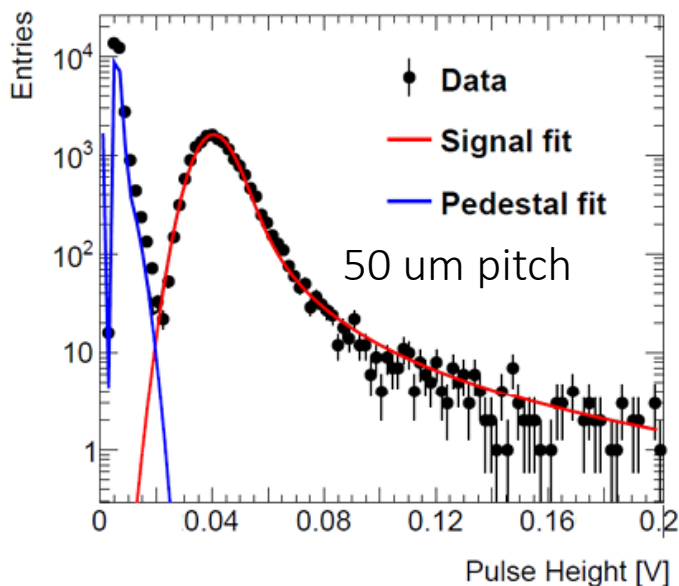
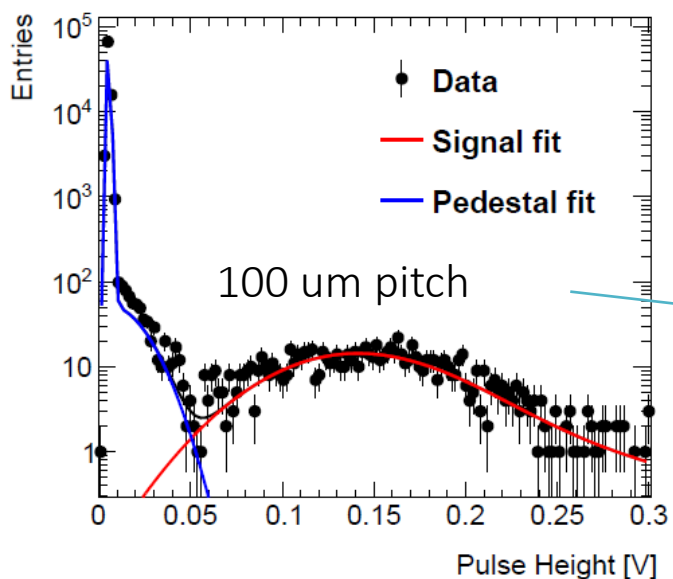


PH dependence on strip length studied w/ a dedicated sample



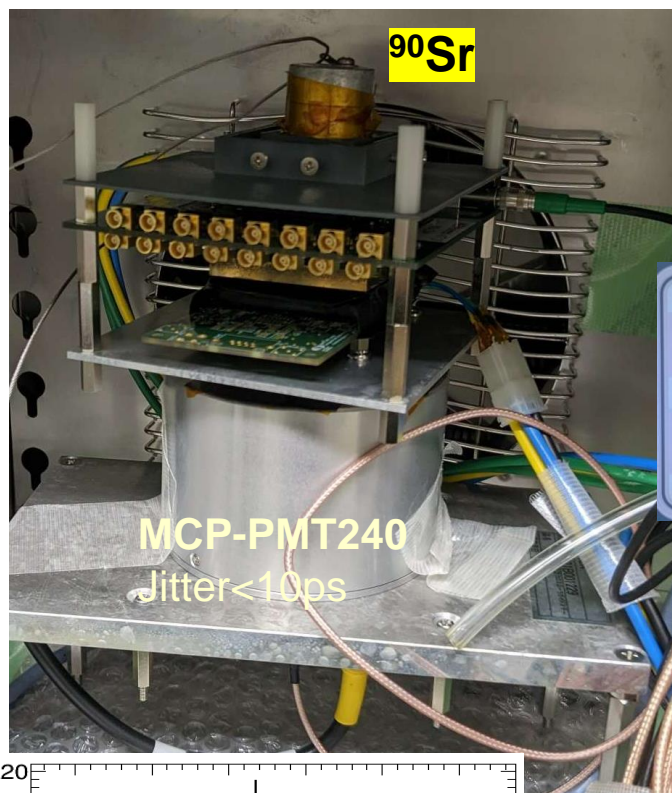
- PH reduced by 60% by inter-strip capacitance at 10 mm, dominating over C_{cp} dependence
- X-talk increase with length

Pixel Pulse Height

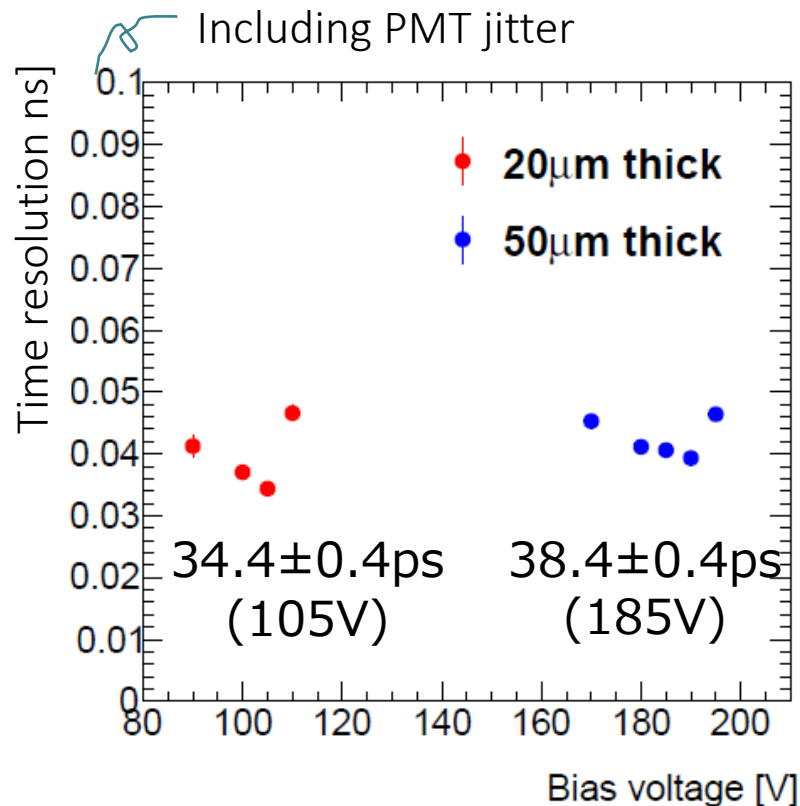


- *PH weakly depends on the pitch*
- *Signal seen also for 50um pitch pixel (as wirebonds are at 100um pitch, readout is not similar to the others; we expect larger signal from TCAD)*

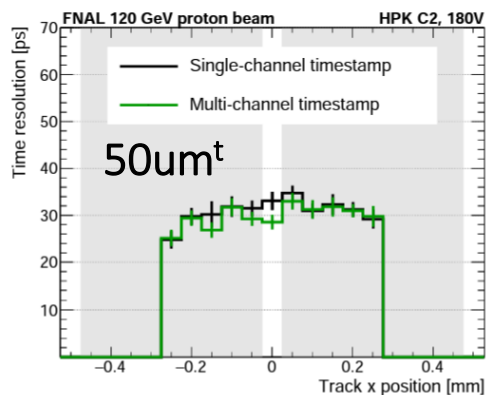
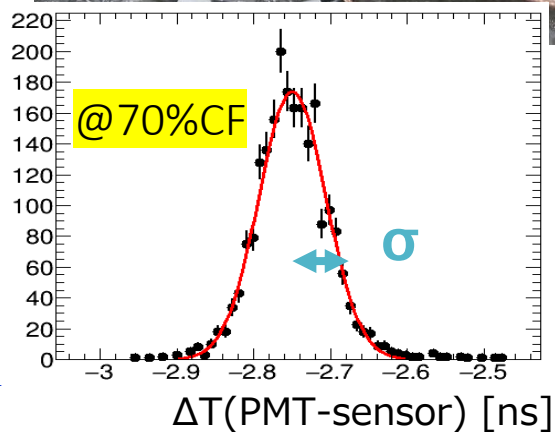
Time Resolution (β)



2x2 pad



- Time resolution is (slightly) better w/ 20 μm
- Not as good as FTBF measurement

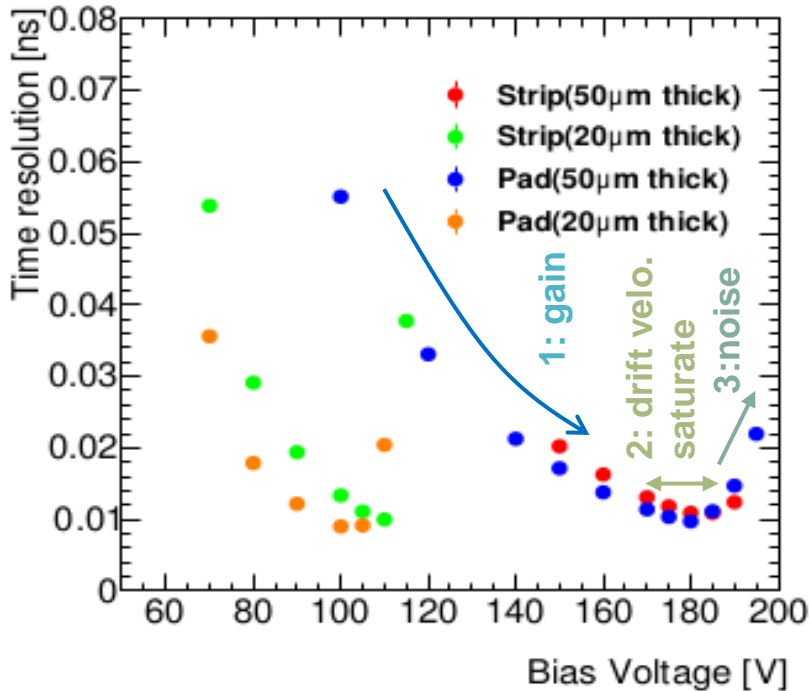


Instrumentation? Beam?
 \Rightarrow Currently testing @ FTBF

Timing resolution (laser)

IR laser: free from Landau effect as charge deposit is uniform along depth

Laser jitter included

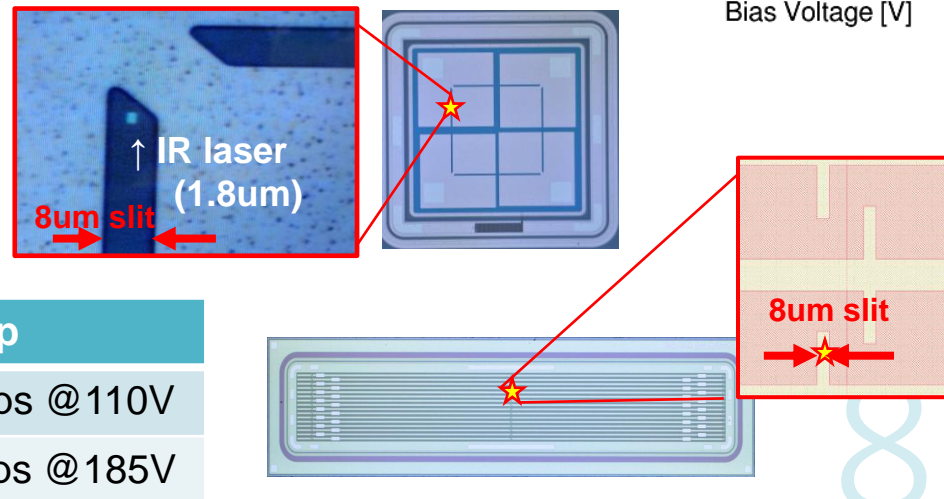
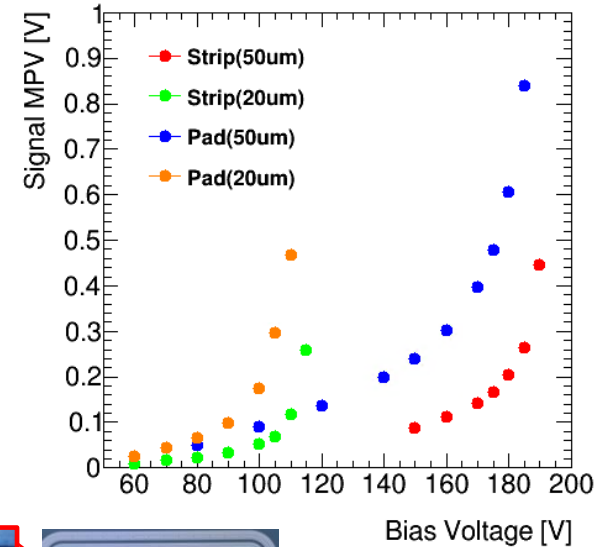


20µm → 80% CF
 50µm → 60% CF
 @ best time resolution

$$\sigma_t^2 = \sigma_{tw}^2 + \sigma_j^2 + \sigma_L^2$$

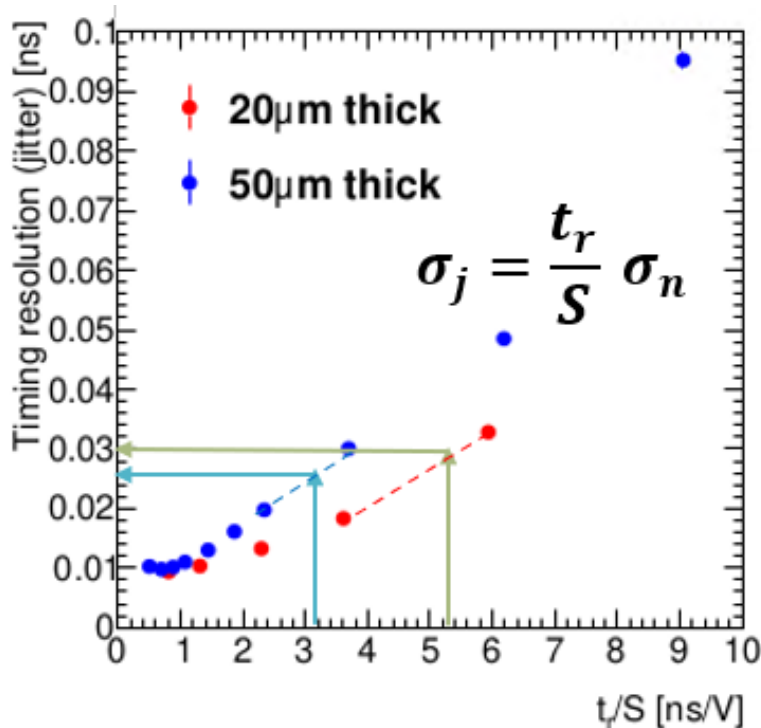
Time-walk is small for larger signal and CFD method...

cf: PH=50mV for β w/ strip (50µm) at 180V



	4chPad	Strip
20µm	8.54 ± 0.03ps @ 105V	10.69 ± 0.03ps @ 110V
50µm	9.81 ± 0.03ps @ 180V	10.83 ± 0.03ps @ 185V

Timing resolution contributions in β

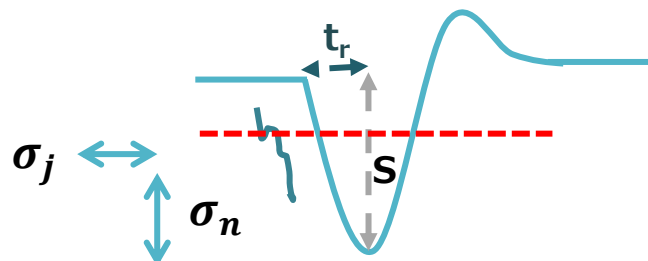


Time resolution w/ laser for varied HV
 t_r/S calculated for $t_r=20\%-80\%$ of S

Dependence as expected as

$$\sigma_j = \frac{t_r}{S} \sigma_n$$

(T_{jitter}) (V_{noise})



$$\sigma_t^2 = \sigma_{tw}^2 + \sigma_j^2 + \sigma_L^2$$

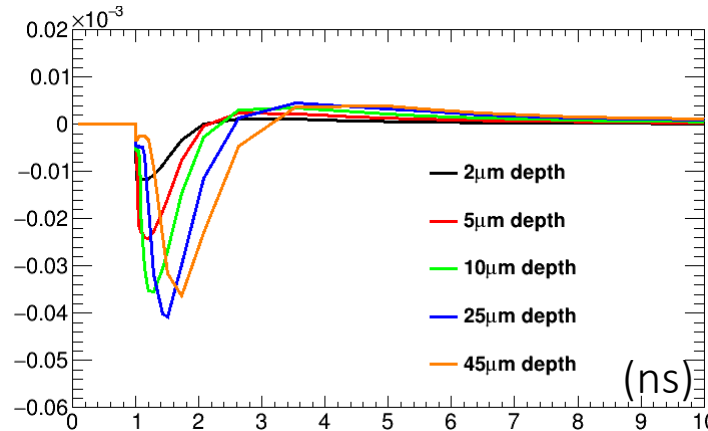
	50 μ m ^t	20 μ m ^t	
σ_t	38.4ps	34.4ps	measured w/ beta (p7)
σ_j	26.8ps	30.7ps	measured t_r/S translated to σ_j
σ_L	27.1 ps	15.5 ps	subtraction of above

Timing resolution deterioration due to Landau effect is smaller for 20 μ m thick sensor

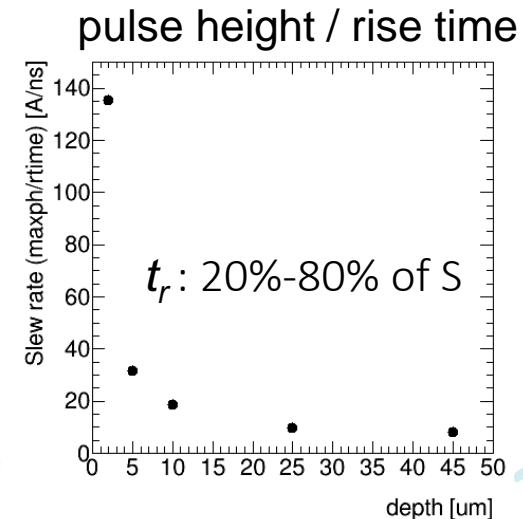
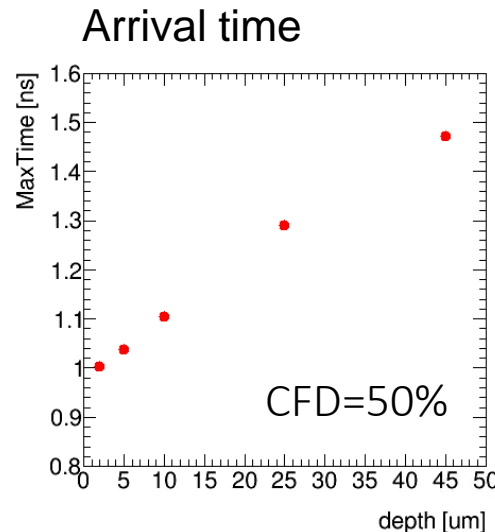
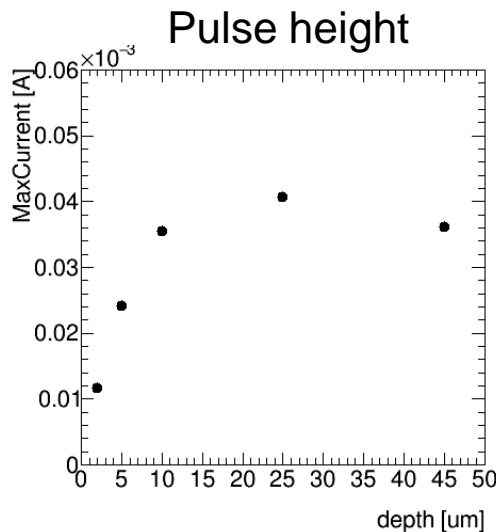
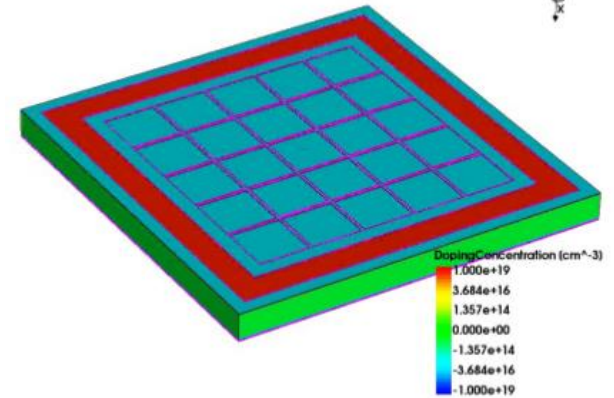
3D TCAD - signal dependence on depth

- ✓ 20 μm thickness has smaller Landau contribution than 50 μm

Signal shapes for charges created at specific depths (D = 2 to 45 μm)



5x5 100 μm pitch pixels



- ✓ PH almost saturated for $D > 20 \mu\text{m}$
- ✓ Landau fluctuation \Rightarrow signal shape deteriorated by late arrival time for $D > 20 \mu\text{m}$

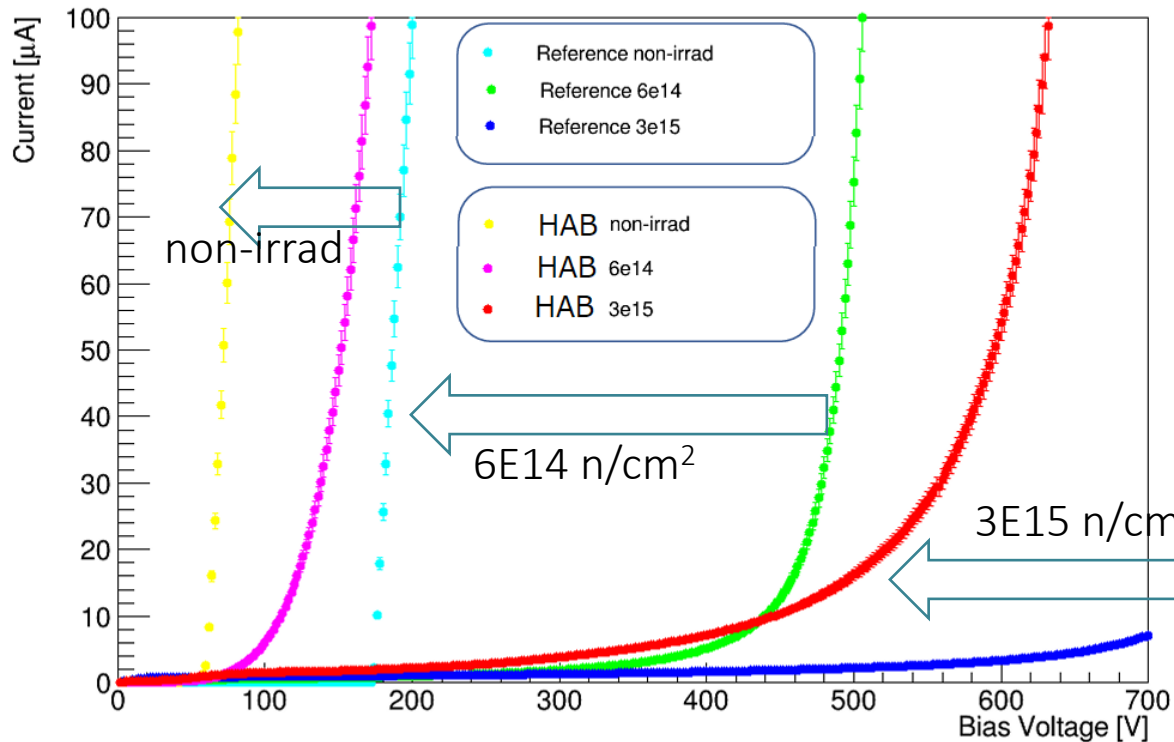
Radiation tolerance improvement – trial1

HPK is investigating to improve their (poor) radiation hardness !

HAB = Half Activated Boron

dope Boron more than required -> insufficient annealing process

-> Borons not in Si lattice work to suppress “acceptor removal” e.g. capture O



Samples: HGTD prototype (DC-LGAD)

- Quite promising results
- V_{gain} at non-irrad needs to tune higher

Radiation tolerance improvement – trial2

Compensation

Result not promising....

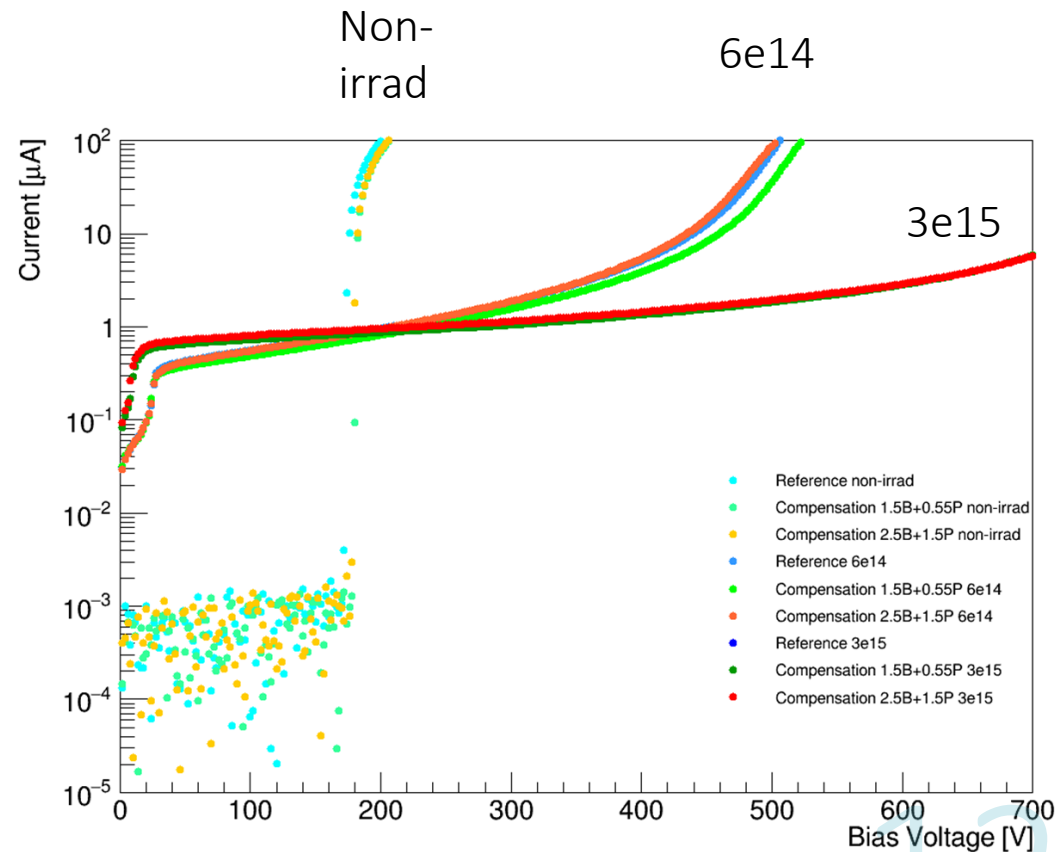
Not much change by two different compensation parameters

$2.5B+1.5P$

$1.5B+0.55P$

Initial compensation works perfect

What does this mean?



How should we understand the results?

$$N_A(\phi) - N_D(\phi) = N_A(0) \cdot e^{-C_A\phi} - N_D(0) \cdot e^{-C_D\phi}$$

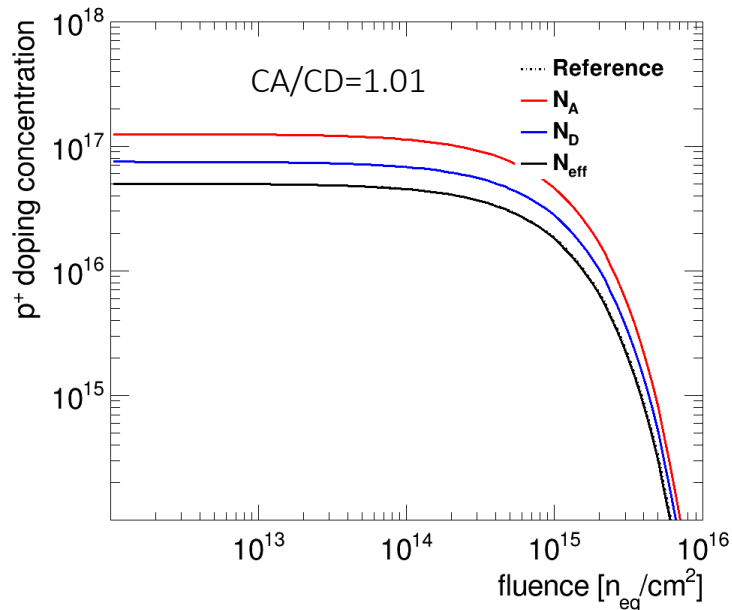
If $C_A = C_D$

$$N_A(\phi) - N_D(\phi) = (N_A(0) - N_D(0)) \cdot e^{-C_A\phi}$$

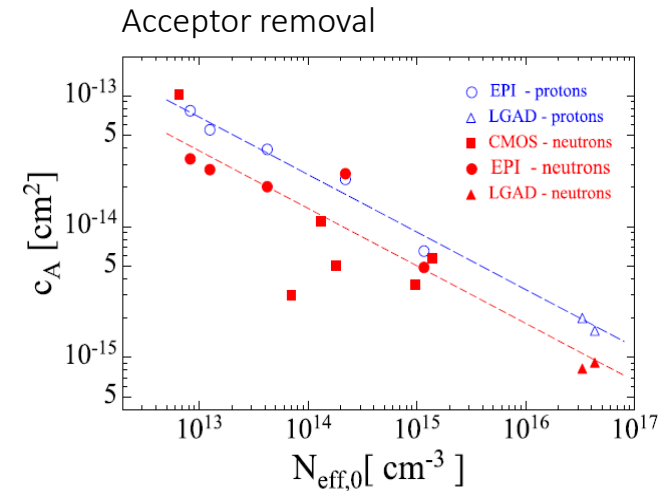
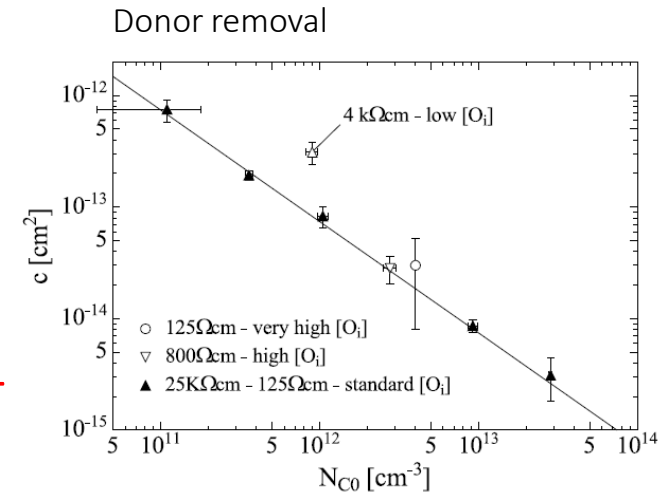
reference

$$N_A(\phi) = N_A(0) \cdot e^{-C_A\phi}$$

Reduction of effective p^+ must be the same as non-compensated case



Previous data



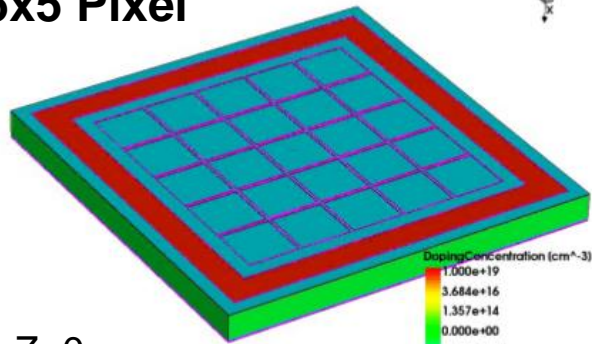
Conclusion

- AC-LGAD sensor parameters are tuned: β signals observed for
strip sensor of 80 μm pitch
pixel sensors down to 50 μm pitch
- Time resolution evaluated w/ β
 - time resolution obtained w/ IR laser is used to decompose
 σ_{Landau} and σ_{jitter}
20 μm thick sensor has smaller σ_{Landau}
more reliable estimate will be soon available from FTBF
- 3D TCAD is ready for qualitative evaluation on time resolution
- HPK is investigating radiation tolerant LGAD: half-activated boron is promising : initial trial of compensation was not promising

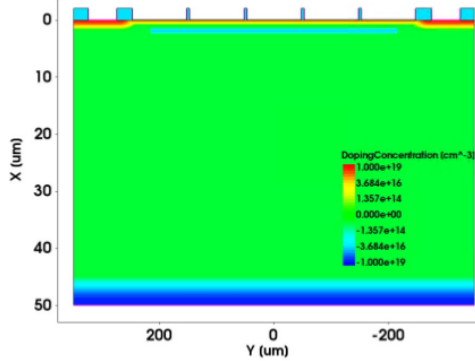
backup

TCAD3D model

5x5 Pixel

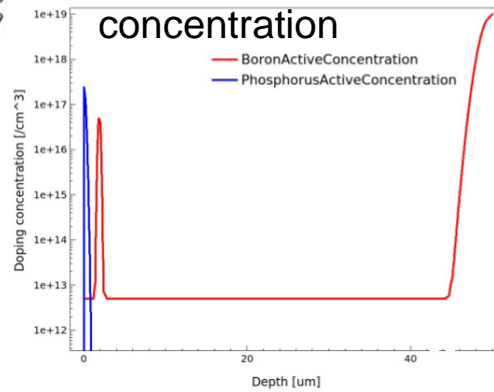


Z=0

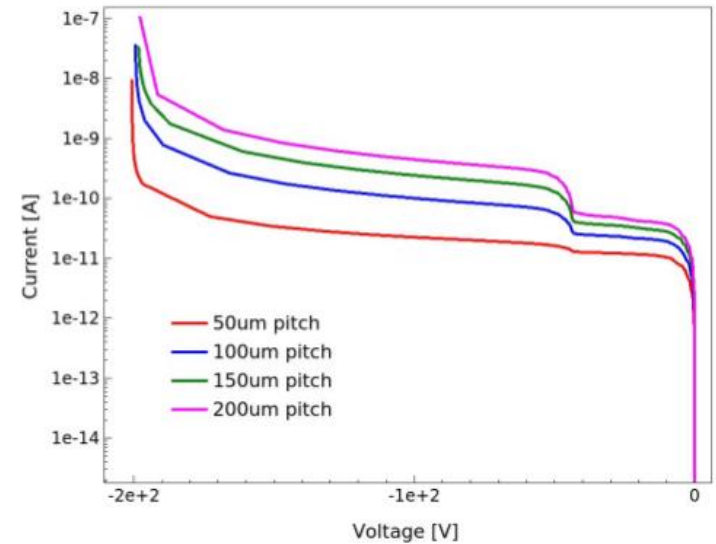


doping

concentration



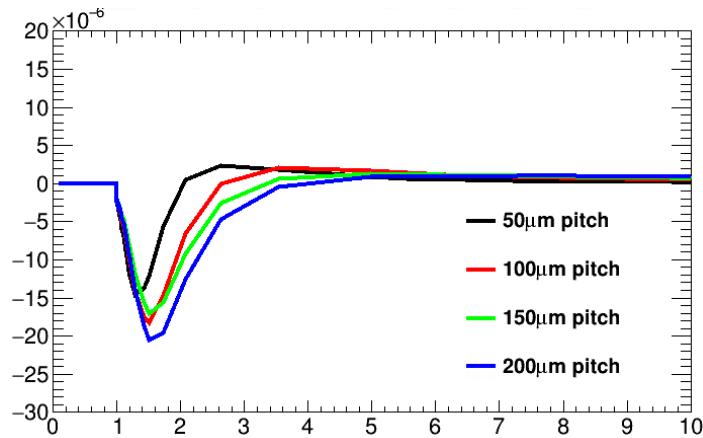
IV simulation @ -20degC



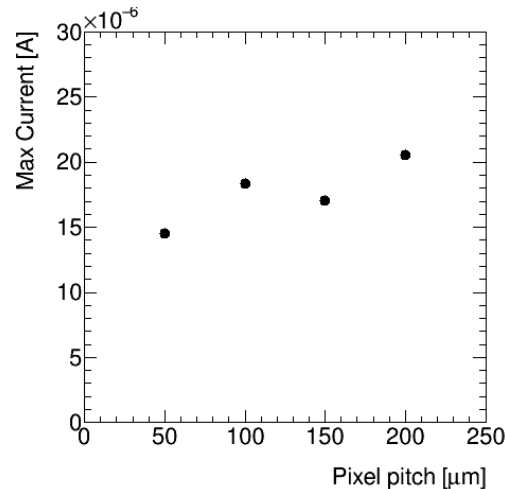
Signal size pitch dependence

Compared different pitch (50, 100, 150, 200 μm)

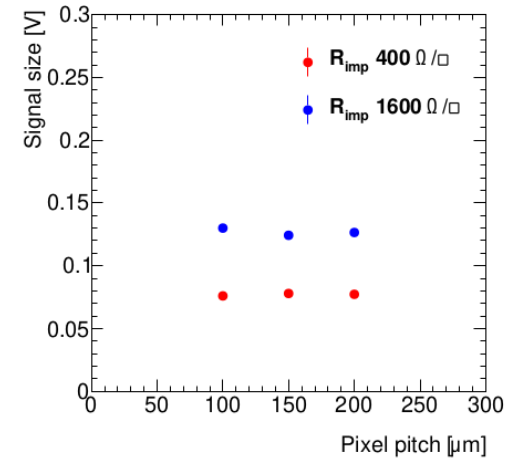
Pulse shape



simulation



measurement

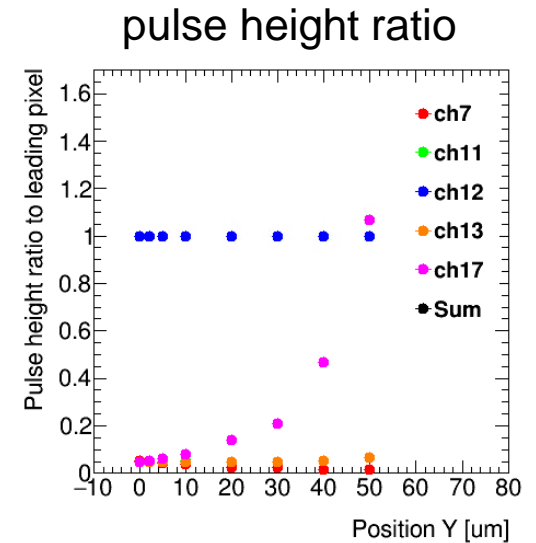
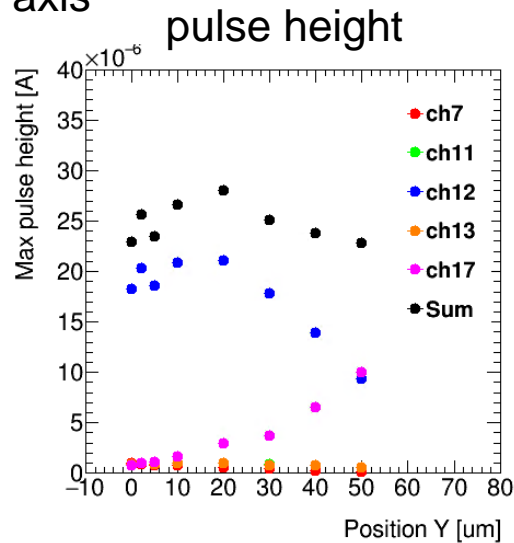
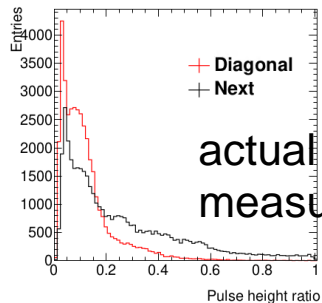


- ✓ signal size is similar to each pitches.
- ✓ simulation and measurement are consistent
- ✓ signal size of 50 μm pitch may be $\sim 90\text{mV}$?

Pixel crosstalk

Change MIP injection point to y axis

0	5	10	15	20
1	6	11	16	21
2	7	12	17	22
3	8	13	18	23
4	9	14	19	24



- ✓ pulse height ratio is 1 between two electrode
- ✓ $\pm 30\mu\text{m}$ area is <30% of xtalk